

# NCE N-Channel Super Trench Power MOSFET

#### Description

The NCEP02580 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### **General Features**

- V<sub>DS</sub> =250V,I<sub>D</sub> =80A
  R<sub>DS(ON)</sub> <18.5mΩ @ V<sub>GS</sub>=10V
- Excellent gate charge x R<sub>DS(on)</sub> product
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

### Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

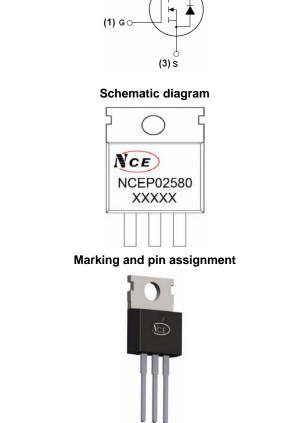
100% ΔVds TESTED!

### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP02580	NCEP02580	TO-220-3L	-	-	-

# Absolute Maximum Ratings (T<sub>c</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	Vds	250	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous	Ι <sub>D</sub>	80	А	
Drain Current-Continuous(Tc=100℃)	I <sub>D</sub> (100℃)	56.6	Α	
Pulsed Drain Current	I <sub>DM</sub>	320	A	
Maximum Power Dissipation	PD	300	W	
Derating factor		2	W/℃	
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	1200	mJ	
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 175	°C	



TO-220-3L top view

(2) D



### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	R <sub>θJC</sub>	0.5	°C/W
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### Electrical Characteristics (T<sub>C</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	250		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =250V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA
On Characteristics (Note 3)	<b>I</b> I		1			
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	2.5		4.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =10V, $I_{D}$ =40A	-	16	18.5	mΩ
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =10V,I <sub>D</sub> =40A	70	-	-	S
Dynamic Characteristics (Note4)			- <b>i</b>	1		
Input Capacitance	Clss		-	5400	-	PF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =125V,V <sub>GS</sub> =0V, F=1.0MHz	-	329	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHZ	-	12	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	18	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =125V,I <sub>D</sub> =40A	-	26	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{G}$ =4.7 $\Omega$	-	41	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	11	-	nS
Total Gate Charge	Qg		-	76.7		nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =125V,I <sub>D</sub> =40A,	-	22.7		nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	20		nC
Drain-Source Diode Characteristics						-
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =80A	-		1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	80	Α
Reverse Recovery Time	t <sub>rr</sub>	$T_{\rm J}$ = 25°C, I <sub>F</sub> = 40	-	140		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	600		nC

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t  $\leq$  10 sec.

3. Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

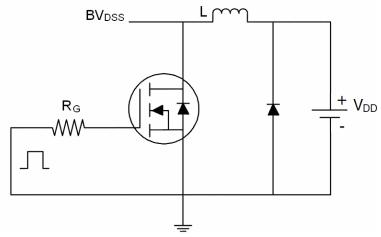
4. Guaranteed by design, not subject to production

5. EAS condition : Tj=25  $^{\circ}$ C,V<sub>DD</sub>=50V,V<sub>G</sub>=10V,L=0.5mH,Rg=25 $\Omega$ 

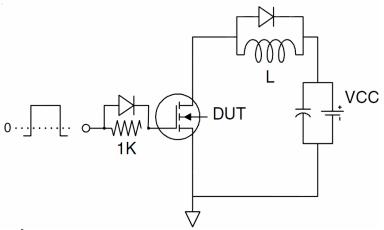


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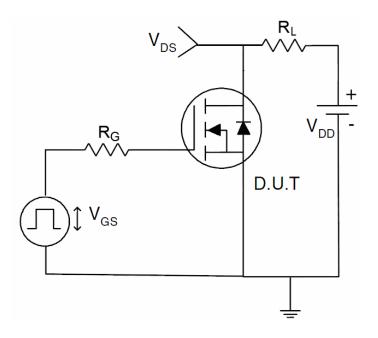
# Test Circuit 1) E<sub>AS</sub> test Circuit



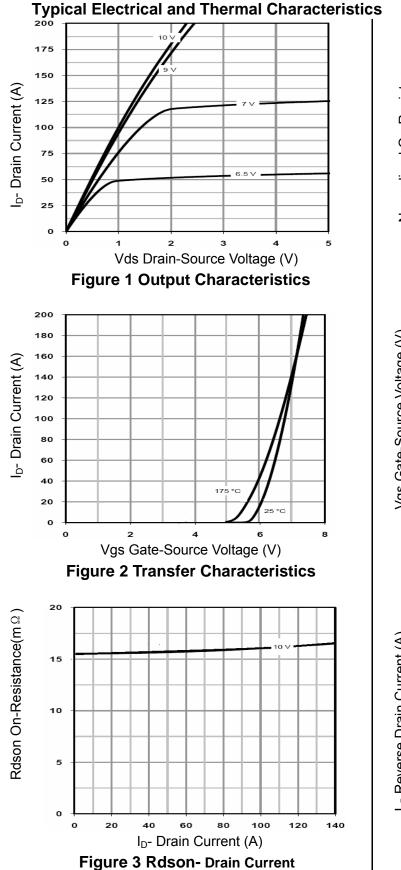
## 2) Gate charge test Circuit

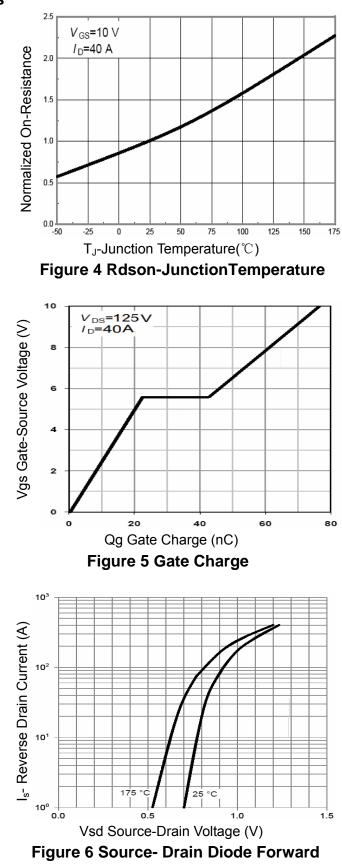


3) Switch Time Test Circuit











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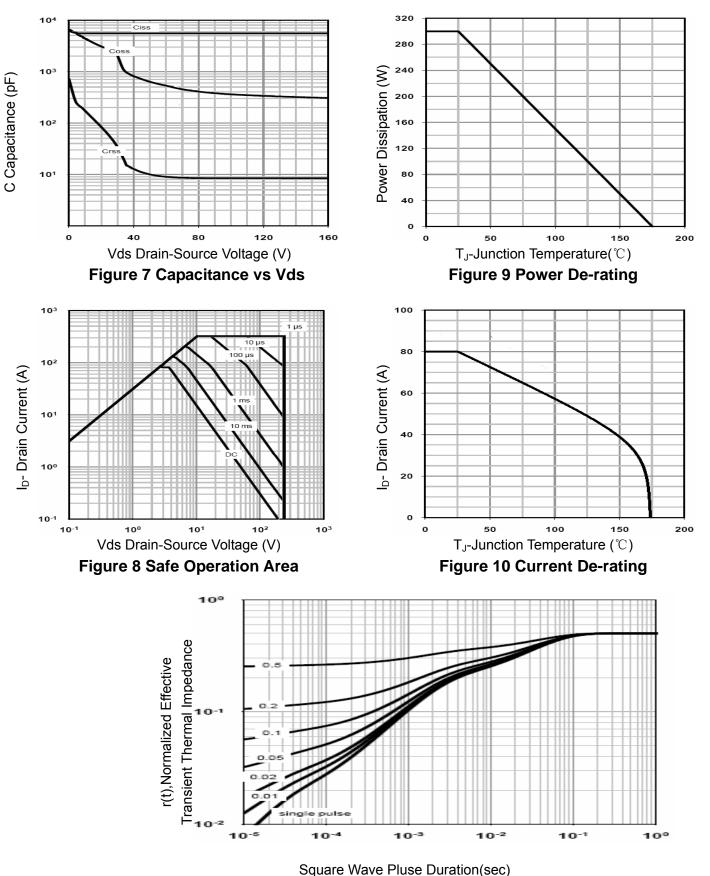
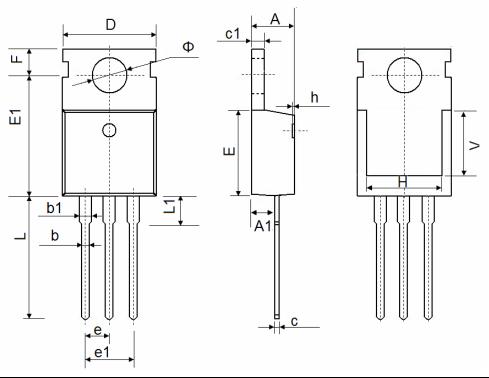


Figure 11 Normalized Maximum Transient Thermal Impedance



# TO-220-3L Package Information



Gumbal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Ф	3.400	3.800	0.134	0.150	



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